AN78MxxNSP Series

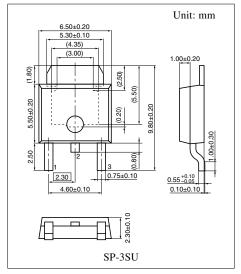
3-pin positive output voltage regulator (500 mA type)

■ Overview

The AN78MxxNSP series is a 3-pin fixed positive output type monolithic voltage regulator housed in surface mounting package. Stabilized fixed output voltage is obtained from unstable DC input voltage with using minimum external components. 9 types of fixed output voltage are available; 5 V, 6 V, 7 V, 8 V, 9 V, 10 V, 12 V, 15 V and 18 V. They can be used widely in power circuits with current capacity up to 500 mA.

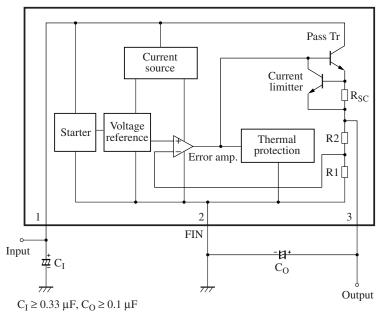
■ Features

- Output voltage: 5V,6V,7V,8V,9V,10V,12V,15V,18V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit
- Built-in ASO (area of safe operation) protection circuit



Note) The package of this product will be changed to lead-free type (SP-3SUA). See the new package dimensions section later of this datasheet.

■ Block Diagram



■ Pin Descriptions

Pin No.		Description
1	Input	Input voltage pin
2	GND	Ground pin (FIN)
3	Output	Output voltage pin

■ Absolute Maximum Ratings

Parameter	Symbol	Range	Unit
Supply voltage *2	V _{CC}	35	V
Supply current *3	I_{CC}	_	mA
Power dissipation *4	P_{D}	_	mW
Operating ambient temperature *1	T _{opr}	-30 to +85	°C
Storage temperature *1	T_{stg}	-55 to +150	°C

Note) 1. *1: Except for the operating ambient temperature and storage temperature, all ratings are for $T_a = 25^{\circ}$ C.

- *2: When V_{CC} of 35 V is applied, the overvoltage protection of ASO protection circuit may shut off the output.
- *3: Since this IC has incorporated a current limiter, the current value does not exceed the rating.
- *4: When Tj exceeds 150°C (designed value), the internal circuit cuts off the output. Note that the relationship between IC power dissipation and the ambient temperature must follow the derating curve.
- 2. This IC is not suitable for car electronics equipment.

■ Electrical Characteristics at T_a = 25°C

• AN78M05NSP (5 V type)

The specified condition $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 10 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25$ °C	4.8	5	5.2	V
Output voltage tolerance	V _{O2}	V_I = 7.5 V to 20 V, I_O = 5 mA to 350 mA T_j = 25°C	4.75		5.25	V
Line regulation 1	REG _{IN1}	$V_I = 7.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	3	100	mV
Line regulation 2	REG _{IN2}	$V_I = 8 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	1	50	mV
Load regulation 1	REG _{L1}	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	20	100	mV
Load regulation 2	REG _{L2}	$I_O = 5 \text{ mA to } 200 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	10	50	mV
Bias current	I _{Bias}	$T_j = 25$ °C	_	4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 8 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 8 \text{ V to } 18 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	62	_	_	dB

· Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	40	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$		2	_	V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		- 0.5		mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$		150		°C

• AN78M06NSP (6 V type)

The specified condition $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 11 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25^{\circ}C$	5.75	6	6.25	V
Output voltage tolerance	V _{O2}	$V_I = 8.5 \text{ V to } 21 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	5.7	_	6.3	V
Line regulation 1	REG _{IN1}	$V_I = 8.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	5	100	mV
Line regulation 2	REG _{IN2}	$V_I = 9 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	1.5	50	mV
Load regulation 1	REG _{L1}	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	20	120	mV
Load regulation 2	REG _{L2}	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	60	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$	_	4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 9 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 9 \text{ V to } 19 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	59	_	_	dB

· Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	45	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2	_	V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	T _{j(TH)}	$I_O = 5 \text{ mA}$	_	150	_	°C

• AN78M07NSP (7 V type)

The specified condition $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 12 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25$ °C	6.7	7	7.3	V
Output voltage tolerance	V _{O2}	$V_I = 9.5 \text{ V to } 22 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_i = 25^{\circ}\text{C}$	6.65	_	7.35	V
Line regulation 1	REG _{IN1}	$V_I = 9.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	6	100	mV
Line regulation 2	REG _{IN2}	$V_I = 10 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG _{L1}	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	20	140	mV
Load regulation 2	REG _{L2}	$I_O = 5 \text{ mA to } 200 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	10	70	mV
Bias current	I _{Bias}	$T_j = 25$ °C	_	4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 10 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 10 \text{ V to } 20 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	57	_	_	dB

Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	48	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2		V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$		1 000		mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5		mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

• AN78M08NSP (8 V type)

The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 14 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25$ °C	7.7	8	8.3	V
Output voltage tolerance	V _{O2}	$V_I = 10.5 \text{ V to } 22 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	7.6	_	8.4	V
Line regulation 1	REG _{IN1}	$V_I = 10.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	6	100	mV
Line regulation 2	REG _{IN2}	$V_I = 11 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG _{L1}	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	25	160	mV
Load regulation 2	REG _{L2}	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	80	mV
Bias current	I _{Bias}	$T_j = 25$ °C	_	4.1	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{\rm I} = 10.5 \text{ V to } 25 \text{ V}, T_{\rm j} = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 11.5 \text{ V to } 21.5 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	56	_	_	dB

Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	48	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2		V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$		1 000		mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5		mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

• AN78M09NSP (9 V type)

The specified condition $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 15 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25$ °C	8.65	9	9.35	V
Output voltage tolerance	V _{O2}	$V_I = 11.5 \text{ V to } 24 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	8.55	_	9.45	V
Line regulation 1	REG _{IN1}	$V_I = 11.5 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	7	100	mV
Line regulation 2	REG _{IN2}	$V_I = 12 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG _{L1}	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	25	180	mV
Load regulation 2	REG _{L2}	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	90	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$	_	4.1	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 12 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 12 \text{ V to } 22 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	56	_	_	dB

Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	60	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$		2		V
output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

• AN78M10NSP (10 V type)

The specified condition $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 16 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25$ °C	9.6	10	10.4	V
Output voltage tolerance	V _{O2}	V_I = 12.5 V to 25 V, I_O = 5 mA to 350 mA T_j = 25°C	9.5	_	10.5	V
Line regulation 1	REG _{IN1}	$V_I = 12.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	7	100	mV
Line regulation 2	REG _{IN2}	$V_I = 13 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG _{L1}	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	25	200	mV
Load regulation 2	REG _{L2}	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	100	mV
Bias current	I_{Bias}	$T_j = 25$ °C	_	4.1	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 13 \text{ V to } 25 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 13 \text{ V to } 23 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	56	_	_	dB

Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	65	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2		V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_0 = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5		mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

• AN78M12NSP (12 V type)

The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 19 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25$ °C	11.5	12	12.5	V
Output voltage tolerance	V _{O2}	$V_I = 14.5 \text{ V to } 27 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25 ^{\circ}\text{C}$	11.4	_	12.6	V
Line regulation 1	REG _{IN1}	$V_I = 14.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	8	100	mV
Line regulation 2	REG _{IN2}	$V_I = 16 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	2	50	mV
Load regulation 1	REG _{L1}	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	25	240	mV
Load regulation 2	REG _{L2}	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	120	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$	_	4.3	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 14.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 15 \text{ V to } 25 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	55	_	_	dB

Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	75	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2	_	V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$	_	1 000		mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5		mV/°C
Thermal protection operating temperature	T _{j(TH)}	$I_O = 5 \text{ mA}$	_	150	_	°C

• AN78M15NSP (15 V type)

The specified condition $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 23 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25^{\circ}C$	14.4	15	15.6	V
Output voltage tolerance	V _{O2}	$V_I = 17.5 \text{ V to } 30 \text{ V}, I_O = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	14.25	_	15.75	V
Line regulation 1	REG _{IN1}	$V_I = 17.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	10	100	mV
Line regulation 2	REG _{IN2}	$V_I = 20 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	3	50	mV
Load regulation 1	REG _{L1}	$I_O = 5 \text{ mA to } 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	25	300	mV
Load regulation 2	REG _{L2}	$I_O = 5 \text{ mA to } 200 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	10	150	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$	_	4.3	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 17.5 \text{ V to } 30 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_O = 5 \text{ mA to } 350 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 18.5 \text{ V to } 28.5 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	54	_	_	dB

· Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	90	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2	_	V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300		mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	$T_{j(TH)}$	$I_O = 5 \text{ mA}$	_	150		°C

• AN78M18NSP (18 V type)

The specified condition $T_j = 25$ °C means that the test should be carried out within so short a test time (within 10 ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Unless otherwise specified, V_I = 27 V, I_O = 350 mA, C_I = 0.33 μF and C_O = 0.1 μF

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V _{O1}	$T_j = 25$ °C	17.3	18	18.7	V
Output voltage tolerance	V _{O2}	$V_1 = 21 \text{ V to } 33 \text{ V}, I_0 = 5 \text{ mA to } 350 \text{ mA}$ $T_j = 25^{\circ}\text{C}$	17.1	_	18.9	V
Line regulation 1	REG _{IN1}	$V_I = 21 \text{ V to } 33 \text{ V}, T_j = 25^{\circ}\text{C}$	_	10	100	mV
Line regulation 2	REG _{IN2}	$V_I = 22 \text{ V to } 33 \text{ V}, T_j = 25^{\circ}\text{C}$	_	5	50	mV
Load regulation 1	REG _{L1}	$I_{O} = 5 \text{ mA to } 500 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	30	360	mV
Load regulation 2	REG _{L2}	$I_{O} = 5 \text{ mA to } 200 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	10	180	mV
Bias current	I_{Bias}	$T_j = 25^{\circ}C$	_	4.4	6	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 21 \text{ V to } 33 \text{ V}, T_j = 25^{\circ}\text{C}$	_	_	0.8	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_{O} = 5 \text{ mA to } 350 \text{ mA}, T_{j} = 25^{\circ}\text{C}$	_	_	0.5	mA
Ripple rejection ratio	RR	$V_I = 22 \text{ V to } 32 \text{ V}, I_O = 100 \text{ mA}, f = 120 \text{ Hz}$	53	_	_	dB

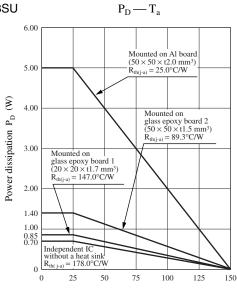
Design reference data

Note) The characteristics listed below are theoretical values based on the IC design and are not guaranteed.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output noise voltage	V _{NO}	f = 10 Hz to 100 kHz	_	100	_	μV
Minimum input/output voltage difference	V _{DIF(min)}	$I_O = 500 \text{ mA}, T_j = 25^{\circ}\text{C}$	_	2	_	V
Output short-circuit current	I _{O(Short)}	$V_I = 35 \text{ V}, T_j = 25^{\circ}\text{C}$	_	300	_	mA
Peak output current	I _{O(Peak)}	$T_j = 25^{\circ}C$	_	1 000	_	mA
Output voltage temperature coefficient	$\Delta V_{\rm O}$ / $T_{\rm a}$	$I_O = 5 \text{ mA}, T_j = 0^{\circ}\text{C to } 125^{\circ}\text{C}$	_	- 0.5	_	mV/°C
Thermal protection operating temperature	T _{j(TH)}	$I_O = 5 \text{ mA}$	_	150	_	°C

■ Application Notes

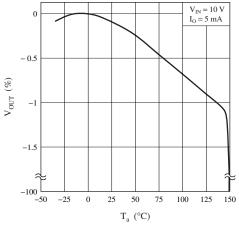
1. P_D — T_a curves of SP-3SU

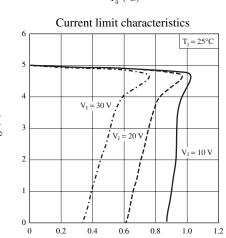


Ambient temperature T_a (°C)

2. Main Characteristics

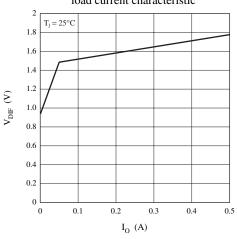
Output voltage temperature characteristic

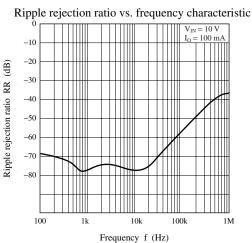




 $I_{O}(A)$

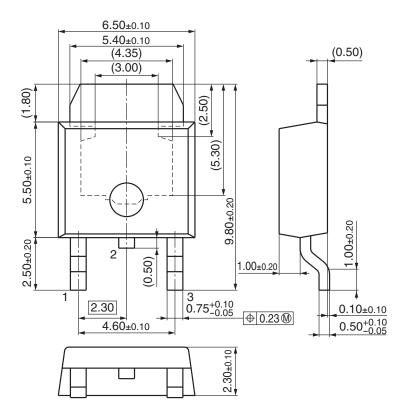
Minimum input/output voltage difference vs. load current characteristic





SFF00012BEB 11

- New Package Dimensions (Unit: mm)
- SP-3SUA (Lead-free package)



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